

## ABSTRACT OF THE DISCLOSURE

Disclosed is an MEMS device using an SOI wafer, the MEMS device comprising a first silicon layer, an insulation layer  
5 formed on the first insulation layer, a second silicon layer formed on the insulation layer, a protective layer formed on the second silicon layer, and a ground hole extending from an upper portion of the protective layer to the first silicon layer and having a conductive material therein, whereby a  
10 handle wafer in the MEMS device is connected to the ground hole without performing any additional wiring or bonding process.